



September 2015

KSP05 / KSP06 NPN Epitaxial Silicon Transistor

Features

- Collector-Emitter Voltage: V_{CEO} = KSP05: 60 V
KSP06: 80 V
- Collector Dissipation: P_C (max.) = 625 mW
- Complement to KSP55/56



Ordering Information

Part Number	Top Mark	Package	Packing Method
KSP05TA	KSP05	TO-92 3L	Ammo
KSP06BU	KSP06	TO-92 3L	Bulk
KSP06TA	KSP06	TO-92 3L	Ammo

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	KSP05	60
		KSP06	80
V_{CEO}	Collector-Emitter Voltage	KSP05	60
		KSP06	80
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current	500	mA
P_C	Collector Power Dissipation	625	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 to 150	$^\circ\text{C}$

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Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit	
BV_{CEO}	Collector-Emitter Breakdown Voltage ⁽¹⁾	KSP05	$I_C = 1\text{ mA}, I_B = 0$	60		V
		KSP06		80		
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100\ \mu\text{A}, I_C = 0$	4		V	
I_{CBO}	Collector Cut-Off Current	KSP05	$V_{CB} = 60\text{ V}, I_E = 0$		0.1	μA
		KSP06		$V_{CB} = 80\text{ V}, I_E = 0$		
I_{CEO}	Collector Cut-Off Current	$V_{CE} = 60\text{ V}, I_B = 0$		0.1	μA	
h_{FE}	DC Current Gain	$V_{CE} = 1\text{ V}, I_C = 10\text{ mA}$	50			
		$V_{CE} = 1\text{ V}, I_C = 100\text{ mA}$	50			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100\text{ mA}, I_B = 10\text{ mA}$		0.25	V	
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 1\text{ V}, I_C = 100\text{ mA}$		1.2	V	
f_T	Current Gain Bandwidth Product	$V_{CE} = 2\text{ V}, I_C = 10\text{ mA}, f = 100\text{ MHz}$	100		MHz	

Note:

1. Pulse test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.